

	Type	Hits	Search Text	DBs	Time Stamp
1	IS&R	328	(257/311.535).CCLS.	USPAT: US-PGPUB	2003/05/19 13:38
2	BRS	26	((257/311.535).CCLS.) and @pd>20021202	USPAT: US-PGPUB	2003/05/19 13:40
3	IS&R	1	("6150689").PN.	USPAT: US-PGPUB	2003/05/19 13:46
4	BRS	10	("4937645" "5188975" "5204286" "5264712" "5336638" "5471079" "5760475" "5783471" "5793076" "5796166").PN.	USPAT	2003/05/19 13:40
5	BRS	4	jp-06053494-\$ did. or jp-07106437-\$ did.	EPO: JPO: DERWENT	2003/05/19 13:48
6	IS&R	1093	(257/306).CCLS.	USPAT: US-PGPUB	2003/05/19 14:05
7	BRS	319	((257/306).CCLS.) and @ad<19960718	USPAT: US-PGPUB	2003/05/19 14:08
8	BRS	4	("4702797" "4978628" "5005072" "5108940").PN.	USPAT	2003/05/19 14:26
9	BRS	2	("5064683" "5414655").PN.	USPAT	2003/05/19 14:26
10	BRS	2	("5361234" "5432732").PN.	USPAT	2003/05/19 14:27
11	BRS	7	("5212114" "5364811" "5406103" "5489791" "5519237" "5532956"	USPAT	2003/05/19 14:28

	Document ID	Pages	Title	Current OR	Current XRef	Inventor
1	US 5689126 A	17	Semiconductor memory device having stacked capacitor	257/306	257/310; 257/E27.086	Takaishi, Yoshihiro
2	US 5519237 A	49	Semiconductor memory device	257/306	257/308; 257/E27.086; 365/149	Itoh, Hiromi et al.
3	US 5623164 A	6	Integrated semiconductor circuit or micromechanical component and process therefore	257/752	257/306; 257/756; 257/758; 257/E21.244	Auer, Stephan et al.
4	US 6127734 A	56	Semiconductor device comprising a contact hole of varying width thru multiple insulating layers	257/774	257/306; 257/750; 257/775; 257/E21.577; 257/E21.579; 257/E21.648; 257/E21.654; 257/E23.019; 438/638; 438/639	Kimura, Hiroshi
5	US 5414655 A	20	Semiconductor memory device having a stack-type capacitor	365/149	257/303; 257/306; 257/E27.086	Ozaki, Tohru et al.
6	US 5432732 A	34	Dynamic semiconductor memory	365/149	257/296; 257/301; 257/304; 257/310; 257/311; 257/E27.085; 438/253; 438/396	Ohmi, Tadahiro